

IN THE CLAIMS:

Please cancel claims 1-2 and 5-6 without prejudice or disclaimer. Please amend claims 3-4 and 7-8 as follows.

Claims 1-2 (Canceled).

Claim 3 (Amended): A method of forming an interlayer dielectric film in a semiconductor device, the method comprising the steps of:

forming a conductive layer patterns of a given pattern and an insulating film spacer on the sidewalls a sidewall of said conductive layer patterns pattern through a common process;

removing said insulating film spacer formed in a region other than a contact plug formation region where a contact plug will be formed; and

forming an interlayer dielectric film on the an entire surface of the semiconductor device.

Claim 4 (Currently Amended): The method of forming an interlayer dielectric film in a semiconductor device as claimed in according to claim 3, wherein said conductive layer patterns are pattern comprises one of a word lines or line and a bit lines line.

Claims 5-6 (Canceled).

Claim 7 (Currently Amended): A method of forming an interlayer dielectric film in a semiconductor device, the method comprising the steps of:

forming conductive layer patterns ~~of a given pattern~~ and an insulating film spacer on the ~~a~~ sidewall of said conductive layer patterns through a common process;

burying a conductive material between said conductive layer patterns;

removing said conductive material ~~only at a given removal region and remaining such that~~ said conductive material remains at remaining regions to form a contact plug; and

burying an interlayer dielectric film between said conductive layer patterns at ~~a said removal region from which said conductive material is removed.~~

Claim 8 (Currently Amended): The method of forming an interlayer dielectric film in a semiconductor device as claimed in according to claim 7, wherein at least one of said conductive layer patterns ~~are comprises one of a word lines or line and a bit lines line.~~